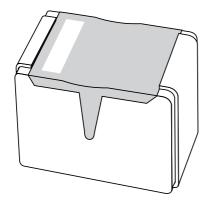
DISCRETE SEMICONDUCTORS

DATA SHEET



BAT254Schottky barrier diode

Product data sheet Supersedes data of 1999 Apr 22 2002 May 28



Schottky barrier diode

BAT254

FEATURES

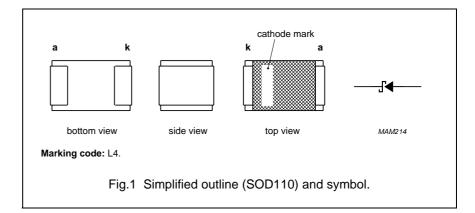
- Low forward voltage
- · Guard ring protected
- Very small ceramic SMD package.

APPLICATIONS

- Ultra high-speed switching
- Voltage clamping
- · Protection circuits
- Blocking diodes.

DESCRIPTION

Planar Schottky barrier diode encapsulated in a SOD110 very small ceramic SMD package.



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _R	continuous reverse voltage		_	30	V
I _F	continuous forward current		-	200	mA
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ s}; \ \delta \le 0.5$	-	300	mA
I _{FSM}	non-repetitive peak forward current	t _p < 10 ms	_	600	mA
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-	125	°C
T _{amb}	operating ambient temperature		-65	+125	°C

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ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V _F	forward voltage	see Fig.2		
		I _F = 0.1 mA	240	mV
		I _F = 1 mA	320	mV
		I _F = 10 mA	400	mV
		I _F = 30 mA	500	mV
		I _F = 100 mA	800	mV
I_R	reverse current	V _R = 25 V; note 1; see Fig.3	2	μΑ
t _{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.5	5	ns
C _d	diode capacitance	$f = 1 \text{ MHz}$; $V_R = 1 \text{ V}$; see Fig.4	10	pF

Note

1. Pulse test: t_p = 300 μ s; δ = 0.02.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	315	K/W

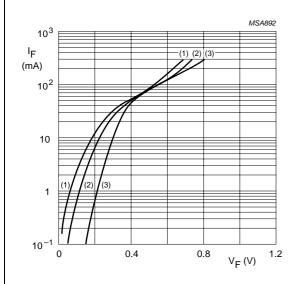
Note

1. Refer to SOD110 standard mounting conditions.

Schottky barrier diode

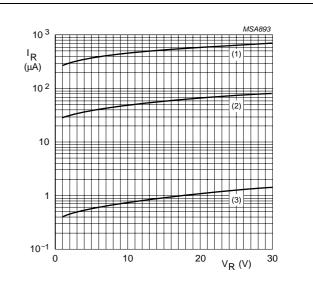
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GRAPHICAL DATA



- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.



- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.3 Reverse current as a function of reverse voltage; typical values.

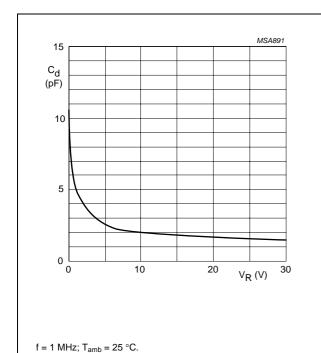
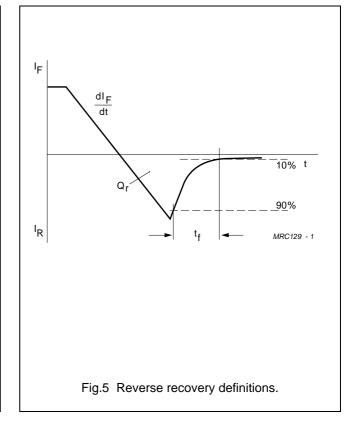


Fig.4 Diode capacitance as a function of reverse voltage; typical values.



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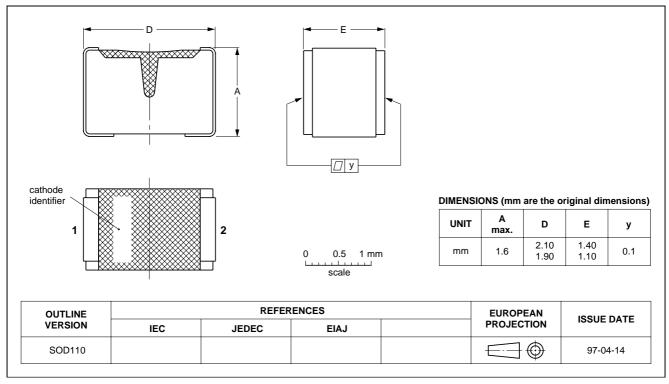
Schottky barrier diode

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PACKAGE OUTLINE

Very small ceramic rectangular surface mounted package

SOD110



Schottky barrier diode

BAT254

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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Printed in The Netherlands 613514/03/pp7 Date of release: 2002 May 28 Document order number: 9397 750 09733

